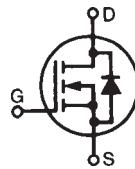


**Polar™ Power MOSFET**  
**HiPerFET™**
**IXFR24N90P**

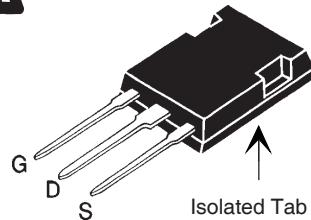
N-Channel Enhancement Mode  
Avalanche Rated  
Fast Intrinsic Diode



**V<sub>DSS</sub>** = 900V  
**I<sub>D25</sub>** = 13A  
**R<sub>DS(on)</sub>** ≤ 460mΩ  
**t<sub>rr</sub>** ≤ 300ns

ISOPLUS247

E153432



G = Gate      D = Drain  
 S = Source

Symbol	Test Conditions	Maximum Ratings	
V <sub>DSS</sub>	T <sub>J</sub> = 25°C to 150°C	900	V
V <sub>DGR</sub>	T <sub>J</sub> = 25°C to 150°C, R <sub>GS</sub> = 1MΩ	900	V
V <sub>GSS</sub>	Continuous	± 30	V
V <sub>GSM</sub>	Transient	± 40	V
I <sub>D25</sub>	T <sub>C</sub> = 25°C	13	A
I <sub>DM</sub>	T <sub>C</sub> = 25°C, pulse width limited by T <sub>JM</sub>	48	A
I <sub>A</sub>	T <sub>C</sub> = 25°C	12	A
E <sub>AS</sub>	T <sub>C</sub> = 25°C	1	J
dV/dt	I <sub>S</sub> ≤ I <sub>DM</sub> , V <sub>DD</sub> ≤ V <sub>DSS</sub> , T <sub>J</sub> ≤ 150°C	15	V/ns
P <sub>D</sub>	T <sub>C</sub> = 25°C	230	W
T <sub>J</sub>		-55 ... +150	°C
T <sub>JM</sub>		150	°C
T <sub>stg</sub>		-55 ... +150	°C
T <sub>L</sub>	Maximum lead temperature for soldering	300	°C
T <sub>SOLD</sub>	Plastic body for 10s	260	°C
V <sub>ISOL</sub>	50/60 Hz, RMS, 1 minute	2500	V~
F <sub>c</sub>	Mounting force	20..120/4.5..27	N/lb.
Weight		5	g

Symbol	Test Conditions (T <sub>J</sub> = 25°C, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA	900		V
V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 1mA	3.5		V
I <sub>GSS</sub>	V <sub>GS</sub> = ± 30V, V <sub>DS</sub> = 0V		± 200	nA
I <sub>DSS</sub>	V <sub>DS</sub> = V <sub>DSS</sub> V <sub>GS</sub> = 0V	T <sub>J</sub> = 125°C	25 2	μA mA
R <sub>DS(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 12A, Note 1		460	mΩ

**Features**

- Silicon chip on Direct-Copper Bond (DCB) substrate
- Isolated mounting surface
- 2500V electrical isolation
- Fast intrinsic diode
- Avalanche rated
- Low package inductance

**Advantages**

- Low gate drive requirement
- High power density

**Applications:**

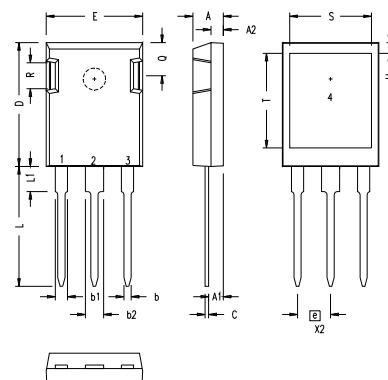
- Switched-mode and resonant-mode power supplies
- DC-DC Converters
- Laser Drivers
- AC and DC motor drives
- Robotics and servo controls

Symbol	Test Conditions (T <sub>J</sub> = 25°C unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
g <sub>fs</sub>	V <sub>DS</sub> = 20V, I <sub>D</sub> = 12A, Note 1	10	16	S
R <sub>GI</sub>	Gate input resistance		1.1	Ω
C <sub>iss</sub>	{ V <sub>GS</sub> = 0V, V <sub>DS</sub> = 25V, f = 1MHz }	7200		pF
C <sub>oss</sub>		490		pF
C <sub>rss</sub>		60		pF
t <sub>d(on)</sub>	{ Resistive Switching Times V <sub>GS</sub> = 10V, V <sub>DS</sub> = 0.5 • V <sub>DSS</sub> , I <sub>D</sub> = 12A R <sub>G</sub> = 1Ω (External) }	46		ns
t <sub>r</sub>		40		ns
t <sub>d(off)</sub>		68		ns
t <sub>f</sub>		38		ns
Q <sub>g(on)</sub>	{ V <sub>GS</sub> = 10V, V <sub>DS</sub> = 0.5 • V <sub>DSS</sub> , I <sub>D</sub> = 12A }	130		nC
Q <sub>gs</sub>		50		nC
Q <sub>gd</sub>		58		nC
R <sub>thJC</sub>			0.54	°C/W
R <sub>thCS</sub>		0.15		°C/W

**Source-Drain Diode**T<sub>J</sub> = 25°C unless otherwise specified)

		Characteristic Values		
		Min.	Typ.	Max.
I <sub>s</sub>	V <sub>GS</sub> = 0V			24 A
I <sub>SM</sub>	Repetitive, pulse width limited by T <sub>JM</sub>			96 A
V <sub>SD</sub>	I <sub>F</sub> = I <sub>s</sub> , V <sub>GS</sub> = 0V, Note 1			1.5 V
t <sub>r</sub>	{ I <sub>F</sub> = 12A, -di/dt = 100A/μs V <sub>R</sub> = 100V, V <sub>GS</sub> = 0V }		300	ns
Q <sub>RM</sub>		1.1		μC
I <sub>RM</sub>		11		A

Note 1: Pulse test, t ≤ 300μs; duty cycle, d ≤ 2%.

**ISOPLUS247 (IXFR) Outline**

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b1	.075	.084	1.91	2.13
b2	.115	.123	2.92	3.12
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
E	.620	.635	15.75	16.13
e	.215 BSC		5.45 BSC	
L	.780	.800	19.81	20.32
L1	.150	.170	3.81	4.32
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83
S	.520	.540	13.21	13.72
T	.620	.640	15.75	16.26
U	.065	.080	1.65	2.03

1 – GATE  
2 – DRAIN (COLLECTOR)  
3 – SOURCE (EMITTER)  
4 – NO CONNECTION

NOTE: This drawing will meet all dimensions requirement of JEDEC outline TO-247AD except screw hole.

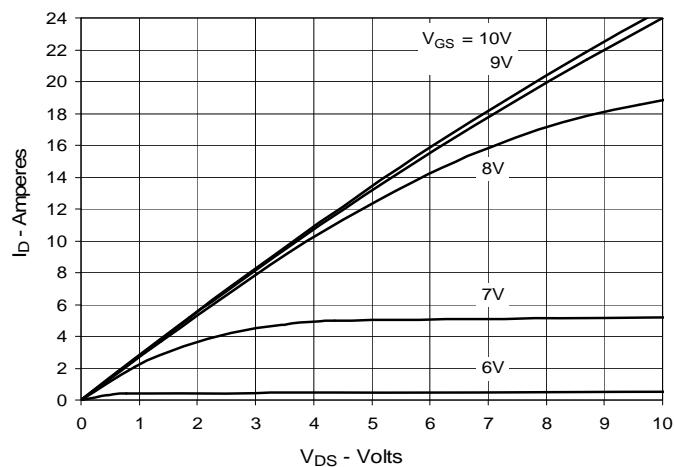
**PRELIMINARY TECHNICAL INFORMATION**

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

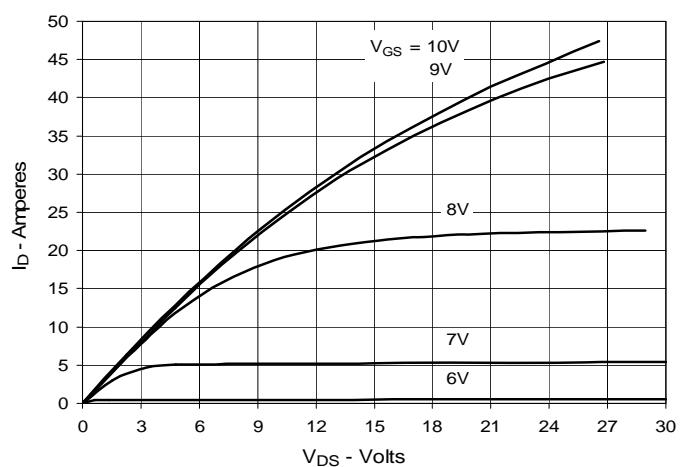
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IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2 4,850,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2 4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

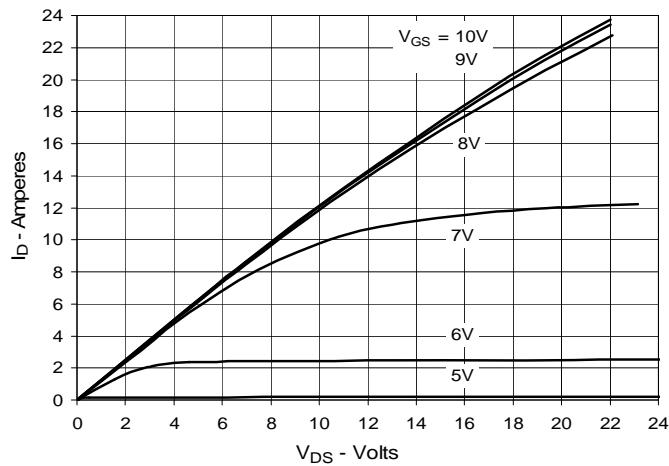
**Fig. 1. Output Characteristics  
@ 25°C**



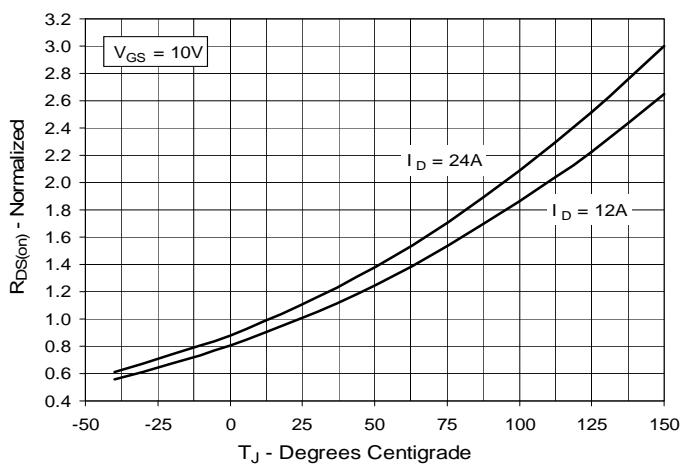
**Fig. 2. Extended Output Characteristics  
@ 25°C**



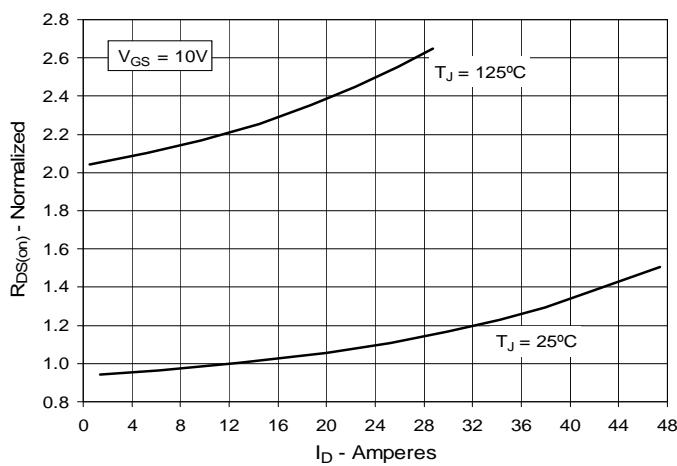
**Fig. 3. Output Characteristics  
@ 125°C**



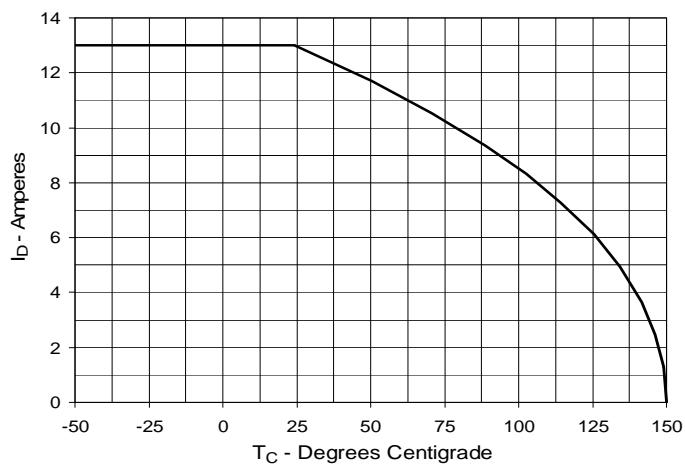
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 12A$  Value  
vs. Junction Temperature**

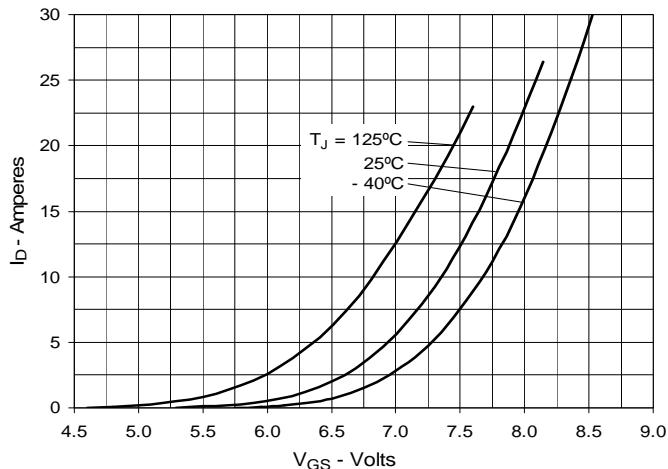
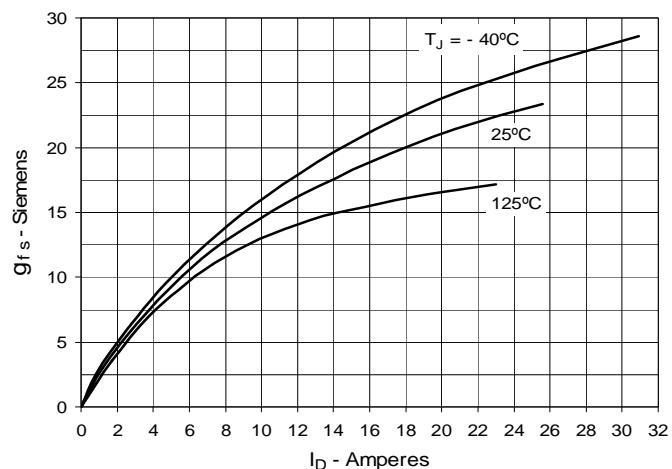
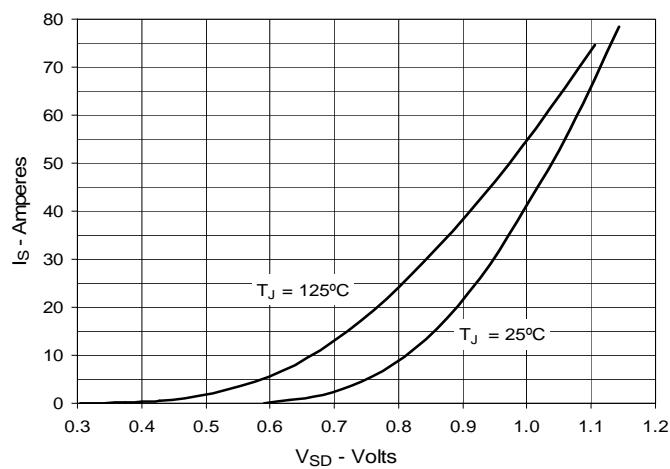
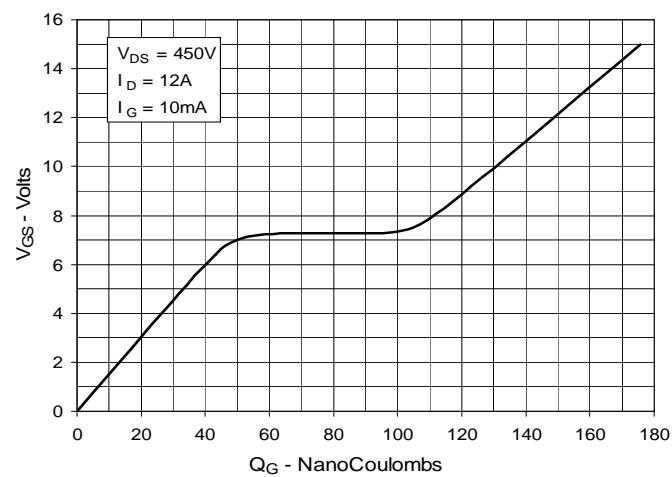
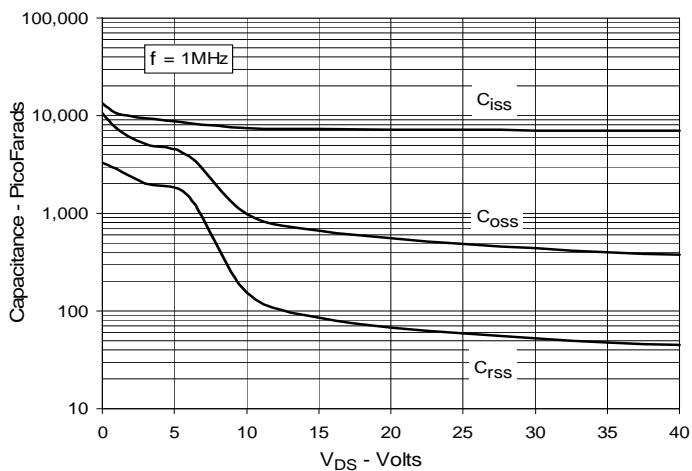
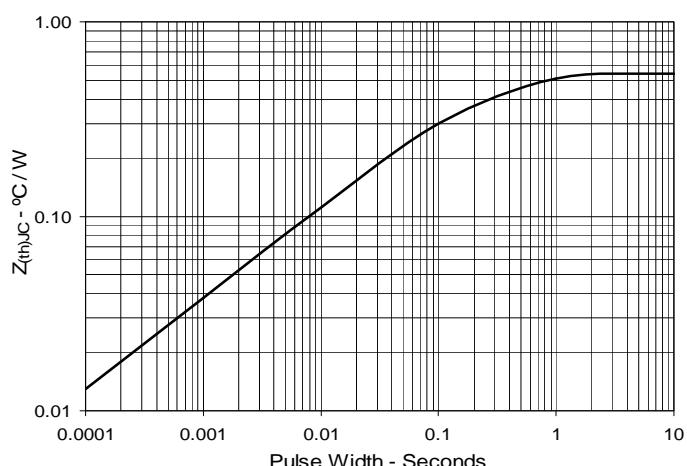


**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 12A$  Value  
vs. Drain Current**



**Fig. 6. Maximum Drain Current vs.  
Case Temperature**



**Fig. 7. Input Admittance****Fig. 8. Transconductance****Fig. 9. Forward Voltage Drop of Intrinsic Diode****Fig. 10. Gate Charge****Fig. 11. Capacitance****Fig. 12. Maximum Transient Thermal Impedance**



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